



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D T _C = +25°C
-40V	$11m\Omega @ V_{GS} = -10V$	-74A
- 4 0V	19mΩ @ $V_{GS} = -4.5V$	-55A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Backlighting

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

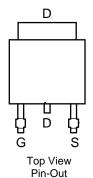
Mechanical Data

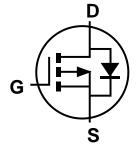
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)

TO252 (DPAK)



Top View





Equivalent Circuit

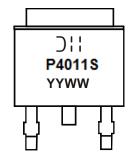
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP4011SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



DII = Manufacturer's Marking P4011S = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Convent (Nate 7) V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	-74 -59	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-14 -11	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-200	Α	
Maximum Body Diode Forward Current (Note 7)	I _S	-70	Α		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%	I _{SM}	-200	Α		
Avalanche Current, L = 1mH (Note 8)	I _{AS}	-22	Α		
Avalanche Energy, L = 1mH (Note 8)	E _{AS}	250	mJ		

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	84	°C/W
Total Power Dissipation (Note 7)		P_{D}	3.1	W
Thermal Resistance, Junction to Ambient (Note 7) Steady State		$R_{ heta JA}$	41	°C/W
Thermal Resistance, Junction to Case		$R_{ heta JC}$	1.4	C/VV
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-40			٧	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μA	$V_{DS} = -32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D		6.5	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	10.8	19	1117.5	$V_{GS} = -4.5V, I_D = -9.8A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		2747			V _{DS} = -20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss		508	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	222	_		1 = 1101112	
Gate Resistance	R_g	_	21.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g		25	_			
Total Gate Charge (V _{GS} = -10V)	Q_g		52	_	nC	$V_{DS} = -20V$,	
Gate-Source Charge	Q_{gs}	_	8.5	_	IIC	$I_D = -9.8A$	
Gate-Drain Charge	Q_{gd}	_	11.8				
Turn-On Delay Time	t _{D(ON)}	_	6.6	_		$V_{GS} = -10V, V_{DD} = -20V,$ $R_{G} = 6\Omega, I_{D} = -1A$	
Turn-On Rise Time	t _R	_	6.5		20		
Turn-Off Delay Time	t _{D(OFF)}	_	222	_	ns		
Turn-Off Fall Time	t _F		138	_			
Reverse Recovery Time	t _{RR}		25		ns	I _F = -9.8A, di/dt = -100A/μs	
Reverse Recovery Charge	Q _{RR}	_	17	_	nC	I _F = -9.8A, di/dt = -100A/μs	

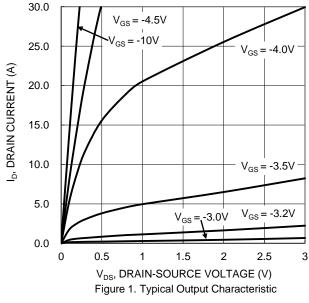
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

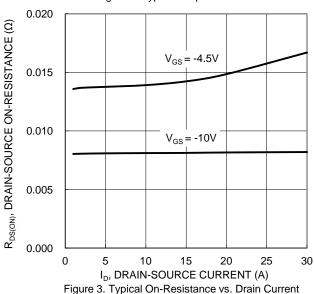
^{8.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

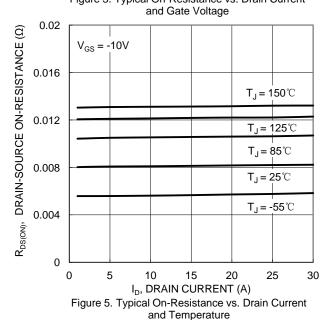
^{9.} Short duration pulse test used to minimize self-heating effect.

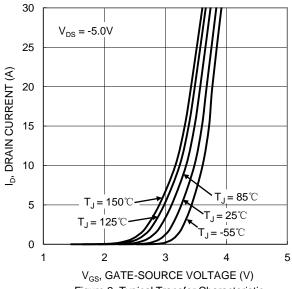
^{10.} Guaranteed by design. Not subject to product testing.

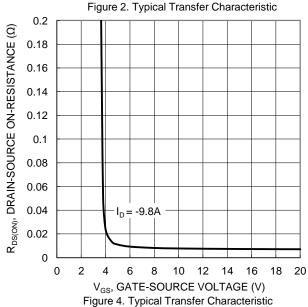


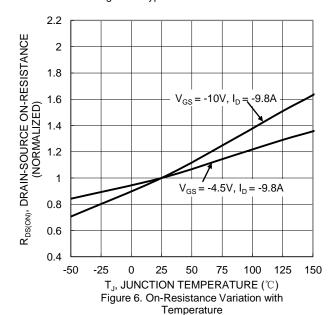














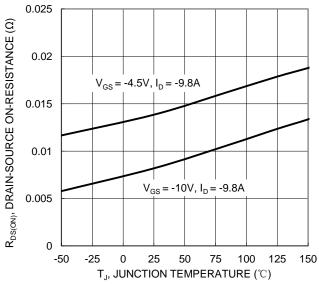
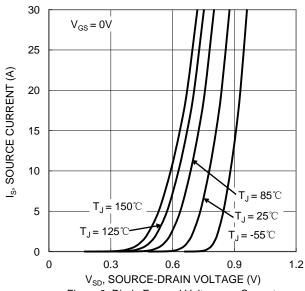
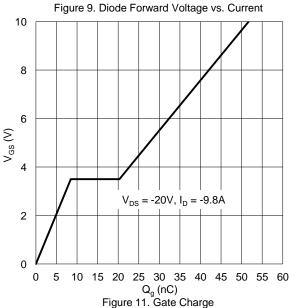


Figure 7. On-Resistance Variation with Temperature





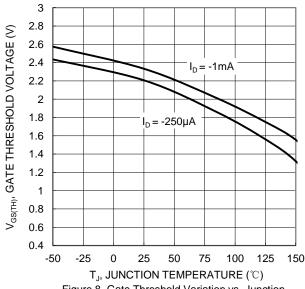
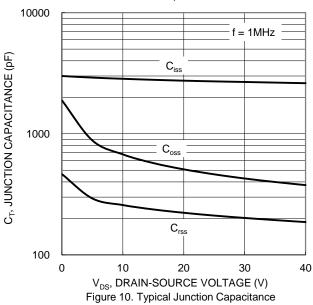
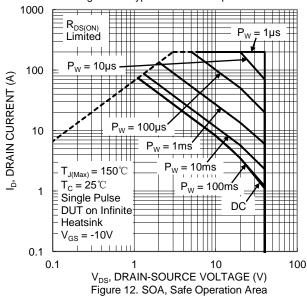


Figure 8. Gate Threshold Variation vs. Junction Temperature





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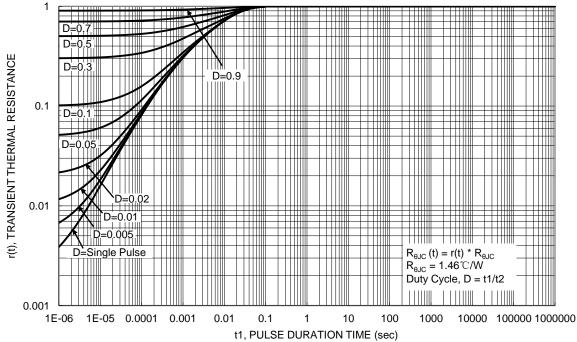


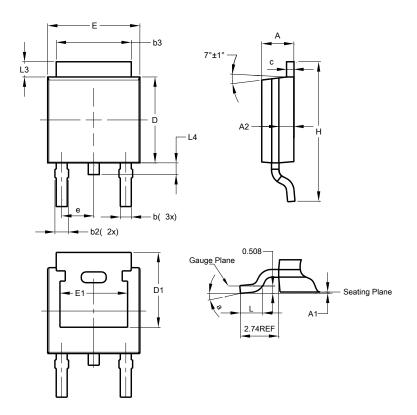
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

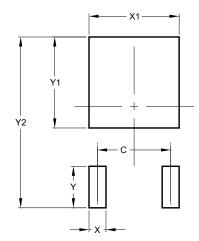


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	1		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
X	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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